



## DOCUMENT CHANGE REQUEST

DCR number            1005            Changes required for: General  
Date: 2016/12/14            Date sent: 2016/06/16  
Status: IMPLEMENTED

Originator: Steve Jeffery  
Organisation: ESCC Executive

Title: Transistors Low Power PNP, based on type 2N5401

Number: 5202/014            Issue: 6

Other documents affected:

Page:

12

Paragraph:

2.4.1

Original wording:

Collector-Base Breakdown Voltage Test Condition: IC = -100mA;

Emitter-Base Breakdown Voltage Test Condition: IC = -10mA

Proposed wording:

Collector-Base Breakdown Voltage Test Condition: IC = -100uA;

Emitter-Base Breakdown Voltage Test Condition: IC = -10uA

[Note - there are also some additional minor editorial and formatting changes]

See attachment (MSWord 2010 file) 5202/014 Issue 7 Draft A.

Justification:

As identified by STMicroelectronics, notified by Aïssa NEHDI: These IC test conditions were changed (typographical errors) during the last update of the spec.

Some additional editorial and formatting errors were found during the subsequent review of 5202/014 Issue 4 which was made when raising this DCR on behalf of STMicroelectronics.

Attachments:

5202014\_draft\_7a.docx

Modifications:

N/A

Approval signature:

A handwritten signature in black ink, appearing to read "R. S. Hart" with a long horizontal stroke extending to the right.

Date signed:

2016-12-14